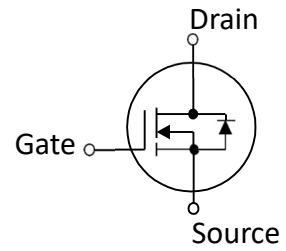
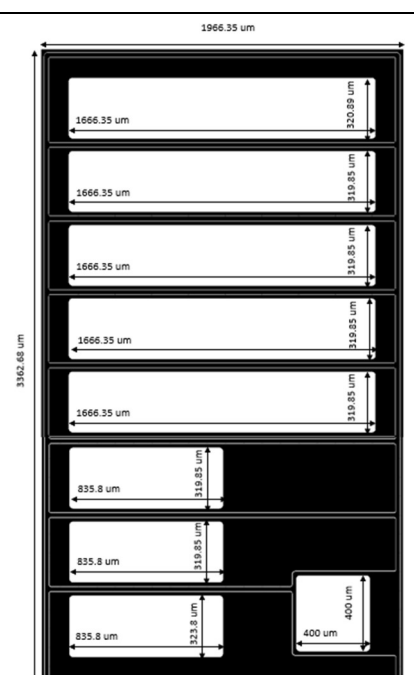


30V N-Channel MOSFET

- Advanced Split Gate Device Design and Processes
- High Reliability Capability
- Sampled CP Probing

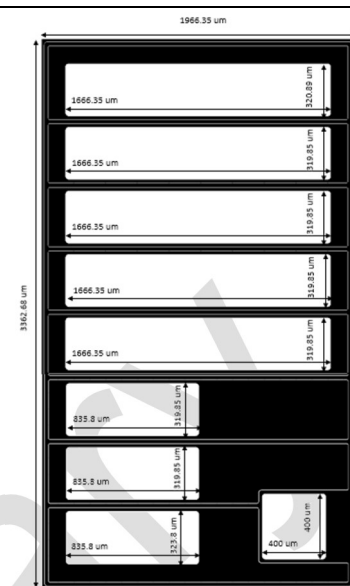
SYMBOL

Electrical Characteristics in C/P Test (T_J at 25 °C)

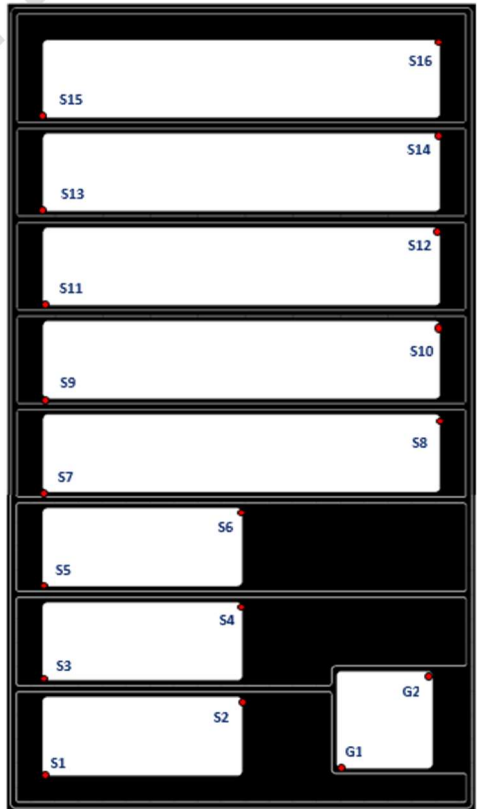
| Symbol | Parameter | Min. | Typ. | Max. | Unit | Test Condition |
|----------------|-----------------------------------|---------------------|------|------|------------|-----------------------------------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | 30 | — | — | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | — | 0.8 | 1.0 | m Ω | $V_{GS} = 5V, I_D = 1A^{(1)}$ |
| $V_{GS(th)}$ | Gate Threshold Voltage | 1 | — | 2.3 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ |
| I_{DSS} | Drain-to-Source Leakage Current | — | — | 1 | μA | $V_{DS} = 25V, V_{GS} = 0V$ |
| I_{GSS} | Gate-to-Source Leakage Current | -100 | — | 100 | nA | $V_{DS} = 0V, V_{GS} = \pm 16V$ |
| T_J, T_{STG} | Operating and Storage Temperature | -55°C to 150°C Max. | | | | |

| Mechanical Data | | Die Drawing |
|---------------------------------|---|---|
| Chip Size ⁽²⁾ | 1966 μm X 3363 μm |  |
| Gate Pad Size | 400 μm X 400 μm | |
| Source Pad Size | 1666 μm X 320 μm x 5 836 μm X 320 μm 836 μm X 324 μm | |
| Scribe Line Width | 60 μm | |
| Wafer Thickness | 50 μm | |
| Wafer Diameter | 200 mm | |
| Gross Die | 3986 EA | |
| Source Metallization | Ti-NiV-Ag / 1-3-1.5kA | |
| Drain Metallization | Ti-Ni-Ag | |
| Passivation | Polyimide | |
| Recommended Storage Environment | Store in original container, in dry nitrogen, 6 months at ambient temperature of 23°C \pm 3°C | |

(1) Pulse Width $t_p = < 1$ mS, Duty Cycle $< 2\%$.

(2) Chip size not include scribe line.

| Specific Assembly Information Bill of Material (BOM) | | Die Drawing |
|--|---------------|---|
| Package Type | DFN5*6 |  |
| Die Attach Method | Soft solder | |
| Soft Solder Composition | Pb,Sn,Ag | |
| Gate Wire Bonding | Cu, 2 mil x 1 | |
| Source Wire Bonding | Cu, clip | |
| Molding Compound Manufacturer | G700HF | |
| Solder Plating Composition | Pure Tin | |

| Position | | | Bonding Diagram Top View |
|----------|---------|---------|--|
| | X (μm) | Y (μm) | |
| ZERO | 0 | 0 |  |
| TOP | 1966.35 | 3362.68 | |
| S1 | 150 | 150 | |
| S2 | 985.8 | 473.8 | |
| S3 | 150 | 545.07 | |
| S4 | 985.8 | 864.92 | |
| S5 | 150 | 936.19 | |
| S6 | 985.8 | 1256.04 | |
| S7 | 150 | 1327.31 | |
| S8 | 1816.35 | 1647.16 | |
| S9 | 150 | 1718.43 | |
| S10 | 1816.35 | 2038.28 | |
| S11 | 150 | 2109.55 | |
| S12 | 1816.35 | 2429.4 | |
| S13 | 150 | 2500.67 | |
| S14 | 1816.35 | 2820.52 | |
| S15 | 150 | 2891.79 | |
| S16 | 1816.35 | 3212.68 | |
| G1 | 1385.8 | 180.775 | |
| G2 | 1785.8 | 580.775 | |

Electrical Characteristics in F/T Test (T_J at 25 °C)

| Symbol | Parameter | Min. | Typ. | Max. | Unit | Test Condition |
|-----------------------------------|-----------------------------------|------|------|------|------|---|
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 1 | μA | V _{DS} =30V, V _{GS} =0V |
| I _{GSSF} | Gate-to-Source Leakage Current | — | — | 100 | nA | V _{DS} =0V, V _{GS} =+16V |
| I _{GSSR} | Gate-to-Source Leakage Current | -100 | — | — | nA | V _{DS} =0V, V _{GS} =-16V |
| BV _{DSS} | Drain-Source Breakdown Voltage | 30 | — | — | V | V _{GS} =0V, I _D =250μA |
| BV _{DSS} | Drain-Source Breakdown Voltage | 30 | — | — | V | V _{GS} =0V, I _D =1mA |
| R _{DS(ON)} | Static Drain-Source On-Resistance | — | — | 1.4 | mΩ | V _{GS} =5V, I _D =20A |
| V _{GS(th)} | Gate Threshold Voltage | 1 | — | 2.3 | V | V _{DS} =V _{GS} , I _D =250μA |
| V _{SD} | Body Diode Forward Voltage | — | — | 1.2 | V | V _{GS} =0V, I _{SD} =20A |
| I _{AS} | Avalanche Current | | | | A | V _{DD} =30V, V _{GS} =10V, R _G =25Ω, L=0.1mH |
| T _J , T _{STG} | Operating and Storage Temperature | -55 | — | 150 | °C | |

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